

BEYOND ATHENA

Epi-GaN

ESA contract

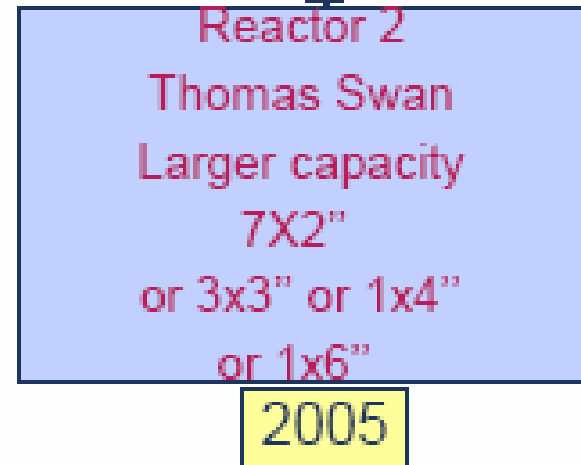
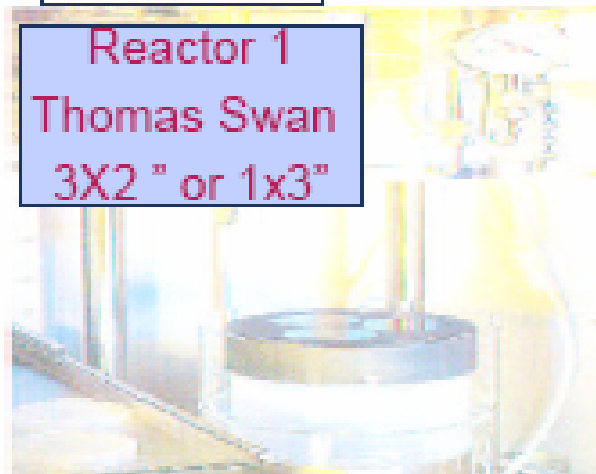
ESA contract 18297/04/NL/CH



Epi-GaN: Increase of GaN epiwafer growth capacity at IMEC

Development of a small-scale facility for epitaxial **GaN** heterostructure wafers

*Technology transfer
HEMT epigrowth*



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Objectives of Epi-GaN

§ To develop a small-scale production facility

§ To develop a new Thomas Swan MOCVD reactor suited to our specific needs and targets

§ To start technology transfer for the existing small size reactor to larger reactor for growth of AlGaN/GaN HEMT structures



- § Service available primarily for ESA partners:
fourth quarter of 2005.
- § Will be available:
 - § HEMT on Sapphire
 - § HEMT on SiC
 - § Eventually: GaN templates for regrowth

Specifications available
on request:

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HEMT on double-side
polished sapphire →

